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SPECIAL ISSUE ON DEVICE TECHNOLOGIES AND CIRCUIT TECHNIQUES FOR POWER MANAGEMENT

FOREWORD

Special Issue on Device Technologies and Circuit Techniques for Power Management	4
. <i>J. J. Welser, S. Kosonocky, T.-J. K. Liu, T. Sakurai, R. Thewes, and B. Zhao</i>	

SPECIAL ISSUE PAPERS

Metal Electrode/High- <i>k</i> Dielectric Gate-Stack Technology for Power Management (<i>Invited Paper</i>)	8
. <i>B. H. Lee, S. C. Song, R. Choi, and P. Kirsch</i>	
Carrier-Transport-Enhanced Channel CMOS for Improved Power Consumption and Performance (<i>Invited Paper</i>)	21
. <i>S. Takagi, T. Irisawa, T. Tezuka, T. Numata, S. Nakaharai, N. Hirashita, Y. Moriyama, K. Usuda, E. Toyoda, S. Dissanayake, M. Shichijo, R. Nakane, S. Sugahara, M. Takenaka, and N. Sugiyama</i>	
Variable-Body-Factor SOI MOSFET With Ultrathin Buried Oxide for Adaptive Threshold Voltage and Leakage Control (<i>Invited Paper</i>)	40
. <i>T. Ohtou, T. Saraya, and T. Hiramoto</i>	
Analytical Modeling of the Suspended-Gate FET and Design Insights for Low-Power Logic	48
. <i>K. Akarvardar, C. Eggimann, D. Tsamados, Y. S. Chauhan, G. C. Wan, A. M. Ionescu, R. T. Howe, and H.-S. P. Wong</i>	
Low-Power and Compact Sequential Circuits With Independent-Gate FinFETs	60
. <i>S. A. Tawfik and V. Kursun</i>	
Design in the Power-Limited Scaling Regime (<i>Invited Paper</i>)	71
. <i>B. Nikolić</i>	
Transistor- and Circuit-Design Optimization for Low-Power CMOS (<i>Invited Paper</i>)	84
. <i>M.-C. Chang, C.-S. Chang, C.-P. Chao, K.-I. Goto, M. Jeong, L.-C. Lu, and C. H. Diaz</i>	
Innovative Materials, Devices, and CMOS Technologies for Low-Power Mobile Multimedia (<i>Invited Paper</i>)	96
. <i>T. Skotnicki, C. Fenouillet-Beranger, C. Gallon, F. Bœuf, S. Monfray, F. Payet, A. Pouydebasque, M. Szczap, A. Farcy, F. Arnaud, S. Clerc, M. Sellier, A. Cathignol, J.-P. Schoellkopf, E. Perea, R. Ferrant, and H. Mingam</i>	
Variation in Transistor Performance and Leakage in Nanometer-Scale Technologies (<i>Invited Paper</i>)	131
. <i>S. Saxena, C. Hess, H. Karbasi, A. Rossoni, S. Tonello, P. McNamara, S. Lucherini, S. Minehane, and C. Dolainsky</i>	
Low-Power SRAMs in Nanoscale CMOS Technologies (<i>Invited Paper</i>)	145
. <i>K. Zhang, F. Hamzaoglu, and Y. Wang</i>	
Device Design and Optimization Methodology for Leakage and Variability Reduction in Sub-45-nm FD/SOI SRAM	152
. <i>S. Mukhopadhyay, K. Kim, and C.-T. Chuang</i>	

(Contents Continued on Page 2)



Nanometer MOSFET Variation in Minimum Energy Subthreshold Circuits (<i>Invited Paper</i>)	163
. <i>N. Verma, J. Kwong, and A. P. Chandrakasan</i>	
Nanometer Device Scaling in Subthreshold Logic and SRAM	175
. <i>S. Hanson, M. Seok, D. Sylvester, and D. Blaauw</i>	
Low Power and Power Management for CMOS—An EDA Perspective (<i>Invited Paper</i>)	186
. <i>J. Kawa</i>	
Reducing Ground-Bounce Noise and Stabilizing the Data-Retention Voltage of Power-Gating Structures	
. <i>S. Kim, C. J. Choi, D.-K. Jeong, S. V. Kosonocky, and S. B. Park</i>	197
Leakage Suppression of Low-Voltage Transient Voltage Suppressor	206
. <i>S.-H. Dai, C.-J. Lin, and Y.-C. King</i>	
Progressive Development of Superjunction Power MOSFET Devices	
. <i>Y. Chen, Y. C. Liang, G. S. Samudra, X. Yang, K. D. Buddharaju, and H. Feng</i>	211
Fully Coupled Nonequilibrium Electron–Phonon Transport in Nanometer-Scale Silicon FETs (<i>Invited Paper</i>)	220
. <i>J. A. Rowlette and K. E. Goodson</i>	
Analysis of Self-Heating Effects in Ultrathin-Body SOI MOSFETs by Device Simulation (<i>Invited Paper</i>)	233
. <i>C. Fiegna, Y. Yang, E. Sangiorgi, and A. G. O’Neill</i>	
Cool Chips: Opportunities and Implications for Power and Thermal Management	245
. <i>S.-C. Lin and K. Banerjee</i>	

REGULAR ISSUE PAPERS

Compound Semiconductor Devices

Microwave Performance of Double δ -Doped High Electron Mobility Transistor With Various Lower/Upper Planar-Doped Ratio Designs	256
. <i>H.-C. Chiu, C.-W. Chen, and Y.-C. Huang</i>	
2-D Analytical Model for Current–Voltage Characteristics and Transconductance of AlGaIn/GaN MODFETs	261
. <i>M. Li and Y. Wang</i>	
Epitaxial Optimization of 130-nm Gate-Length InGaAs/InAlAs/InP HEMTs for High-Frequency Applications	268
. <i>M. Malmkvist, S. Wang, and J. V. Grahn</i>	

Molecular and Organic Devices

Simulation of a Low-Voltage Organic Transistor Compatible With Printing Methods	276
. <i>A. Takshi, A. Dimopoulos, and J. D. Madden</i>	

Nanoelectronics

A Computational Study of Vertical Partial-Gate Carbon-Nanotube FETs	283
. <i>Y. Yoon, J. Fodor, and J. Guo</i>	
An Analytical Derivation of the Density of States, Effective Mass, and Carrier Density for Achiral Carbon Nanotubes	289
. <i>D. Akinwande, Y. Nishi, and H.-S. P. Wong</i>	
Predicting the Performance of Low-Loss On-Chip Inductors Realized Using Carbon Nanotube Bundles	298
. <i>A. Nieuwoudt and Y. Massoud</i>	
Computational Study of the Ultimate Scaling Limits of CNT Tunneling Devices.	313
. <i>S. Poli, S. Reggiani, A. Gnudi, E. Gnani, and G. Baccarani</i>	

Optoelectronics, Displays, and Imaging

A Monolithically Integrated Dual-Wavelength Tunable Photodetector Based on a Taper GaAs Substrate.	322
. <i>J. Lv, H. Huang, Y. Huang, X. Ren, A. Miao, Y. Li, H. Du, Q. Wang, and S. Cai</i>	
Hexagonal a-Si:H TFTs: A New Advanced Technology for Flat-Panel Displays	329
. <i>H. Lee, J.-S. Yoo, C.-D. Kim, I.-B. Kang, and J. Kanicki</i>	
Characterization of Short-Wavelength-Selective a-Si:H MSM Photoconductors for Large-Area Digital-Imaging Applications.	337
. <i>F. Taghibakhsh, I. Khodami, and K. S. Karim</i>	

Reliability

Hole Distributions in Erased NROM Devices: Profiling Method and Effects on Reliability	343
. <i>A. Padovani, L. Larcher, and P. Pavan</i>	
Tradeoff Characteristics Between Resistivity and Reliability for Scaled-Down Cu-Based Interconnects	
. <i>S. Yokogawa, K. Kikuta, H. Tsuchiya, T. Takewaki, M. Suzuki, H. Toyoshima, Y. Kakuhara, N. Kawahara, T. Usami, K. Ohto, K. Fujii, Y. Tsuchiya, K. Arita, K. Motoyama, M. Tohara, T. Taiji, T. Kurokawa, and M. Sekine</i>	350

Silicon Devices

SiGe HBTs With Normal High-Speed Emitter-Up and Reverse Low-Power Collector-Up Operation	358
. <i>L. J. Choi, A. Sibaja-Hernandez, R. Venegas, S. Van Huynenbroeck, and S. Decoutere</i>	
A Novel Low-Power and High-Speed SOI SRAM With Actively Body-Bias Controlled (ABC) Technology for Emerging Generations	365
. <i>Y. Hirano, M. Tsujiuchi, Y. Maki, T. Iwamatsu, Y. Ishii, A. Miyanishi, Y. Tsukamoto, K. Nii, T. Ipposhi, H. Oda, S. Maegawa, and Y. Inoue</i>	
Dual-Material Double-Layer Gate Stack SON MOSFET: A Novel Architecture for Enhanced Analog Performance—Part I: Impact of Gate Metal Workfunction Engineering	372
. <i>P. Kasturi, M. Saxena, M. Gupta, and R. S. Gupta</i>	
Dual-Material Double-Layer Gate Stack SON MOSFET: A Novel Architecture for Enhanced Analog Performance—Part II: Impact of Gate-Dielectric Material Engineering	382
. <i>P. Kasturi, M. Saxena, M. Gupta, and R. S. Gupta</i>	
Statistical Model for Random Telegraph Noise in Flash Memories	388
. <i>C. Monzio Compagnoni, R. Gusmeroli, A. S. Spinelli, A. L. Lacaita, M. Bonanomi, and A.Visconti</i>	
A Comparative Study of Two Different Schemes to Dopant Segregation at NiSi/Si and PtSi/Si Interfaces for Schottky Barrier Height Lowering	396
. <i>Z. Qiu, Z. Zhang, M. Östling, and S.-L. Zhang</i>	
A Novel NAND Flash Memory With Asymmetric S/D Structure Using Fringe-Field-Induced Inversion Layer	404
. <i>K.-T. Park, J.-S. Sel, J. Choi, Y. Song, C. Kim, and K. Kim</i>	
Modeling the Centroid and the Inversion Charge in Cylindrical Surrounding Gate MOSFETs, Including Quantum Effects.	411
. <i>J. B. Roldán, A. Godoy, F. Gámiz, and M. Balaguer</i>	

Solid-State Device Phenomena

Flicker-Noise Impact on Scaling of Mixed-Signal CMOS With HfSiON	417
. <i>Y. Yasuda, T.-J. K. Liu, and C. Hu</i>	
Quantum Modeling of Thermoelectric Properties of Si/Ge/Si Superlattices	423
. <i>A. Bulusu and D. G. Walker</i>	

Solid-State Power and High Voltage

Evaluation of RF-Stress Effect on Class-E MOS Power-Amplifier Efficiency	430
. <i>J. S. Yuan and J. Ma</i>	
Analysis of a Narrow-Base Lateral IGBT With Double Buried Layer for Junction-Isolated Smart-Power Technologies	435
. <i>B. Bakeroot, J. Doutrelaigne, P. Vanmeerbeek, and P. Moens</i>	
Improving the Performance of Superjunction Devices Having Fixed Charge in Isolation and Termination Oxide Layers	446
. <i>S. Balaji and S. Karmalkar</i>	

Solid-State Sensors and Actuators

Detailed Study of Amorphous Silicon Ultraviolet Sensor With Chromium Silicide Window Layer	452
. <i>D. Caputo, G. de Cesare, A. Nascetti, and M. Tucci</i>	

BRIEFS

Low-Noise Avalanche Photodiode in Standard 0.35- μ m CMOS Technology	457
. <i>L. Pancheri, M. Scandiuazzo, D. Stoppa, and G.-F. Dalla Betta</i>	
Miniature RF Test Structure for On-Wafer Device Testing and In-Line Process Monitoring	462
. <i>M.-H. Cho, R. Lee, A.-S. Peng, D. Chen, C.-S. Yeh, and L.-K. Wu</i>	
Power Semiconductor Device Figure of Merit for High-Power-Density Converter Design Applications	466
. <i>H. Wang, F. Wang, and J. Zhang</i>	

ANNOUNCEMENTS

Call for Papers—Joint Special Issue of IEEE TRANSACTIONS ON ELECTRON DEVICES and IEEE TRANSACTIONS ON NANOTECHNOLOGY on Nanowire Electronics	471
Call for Nominations—2006–2007 Region 9 Biennial Outstanding Student Paper Award.	473
Call for Papers—2008 Symposium on VLSI Technology (VLSI TECH).	474
Call for Papers—2008 IEEE Radio Frequency Integrated Circuits Symposium (RFIC)	475

About the Cover: Self-consistent simulation of the temperature profile of a modern silicon integrated circuit from “Cool Chips: Opportunities and Implications for Power and Thermal Management” by Lin *et al.*